## A Critical Size of SnO<sub>2</sub> Nanoparticles for Li-Ion Cells

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Recently, many efforts have been made to improve the electrochemical properties of SnO<sub>2</sub> electrode for Li-ion cells [1-4]. Li et al. reported that SnO<sub>2</sub> nanofibers protruding from а current-collector surface effectively accommodated the volume change [2]. This anode material retained excellent cycling stability at the high C rate. Thin-film SnO<sub>2</sub> was also studied for the same purpose [3,4]. However, these electrodes are not economically feasible for Li-ion cells.

 $SnO_2$  nanocrystals with a different size,  $\sim 3$ and  $\sim 8$  nm, were synthesized using SnCl<sub>4</sub> and triethylenediamine (TEDA) as a structural-directing agent by hydrothermal method at 110°C and 200°C, respectively (Fig. 1). Their electrochemical properties were measured using coin-type half cells (2016 type). Results showed that ~3 nm-sized nanoparticles had superior capacity and cycling stability compared to ~8 nm-sized ones. The ~3 nm-sized SnO<sub>2</sub> nanoparticles exhibited initial capacity of 740 mAh/g with negligible capacity fading even at a high rate of 1800 mA/g (Fig. 2). The electrochemical properties of ~3 nm-sized SnO<sub>2</sub> nanoparticles were superior to those of thin-film analogues. TEM and XRD confirmed that ~3 nm-sized SnO<sub>2</sub> after 30 cycles did not aggregate into large Sn clusters and maintained its particle size, in contrast to the ~8 nm-sized one.



Figure 1. TEM images of  $SnO_2$  nanoparticles with an average particle size of ~3 nm (left) and ~8 nm (right).



Figure 2. Capacity retention of  $SnO_2$  nanoparticles cycled at the discharge rate of 300 mA/g and charge rate of 1800 mA/g between 0 and 1.2 V.

## References

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